

Data sheet acquired from Harris Semiconductor

January 1997

NOT RECOMMENDED FOR NEW DESIGNS Use CMOS Technology

· Buffered Inputs

Features

- Typical Propagation Delay: 6.4ns at V_{CC} = 5V, $T_A = 25^{\circ}C, C_L = 50pF$
- CD74FCT540
 - Invertina
- CD74FCT541
 - Noninverting
- SCR Latchup Resistant BiCMOS Process and **Circuit Design**
- Speed of Bipolar FAST™/AS/S
- 64mA Output Sink Current
- Output Voltage Swing Limited to 3.7V at V_{CC} = 5V
- Controlled Output Edge Rates
- Input/Output Isolation to V_{CC}
- . BiCMOS Technology with Low Quiescent Power

CD74FCT540, CD74FCT541

BiCMOS FCT Interface Logic, Octal Buffers/Line Drivers, Three-State

Description

The CD74FCT540 and CD74FCT541 octal buffers/line drivers use a small geometry BiCMOS technology. The output stage is a combination of bipolar and CMOS transistors that limits the output HIGH level to two diode drops below V_{CC}. This resultant lowering of output swing (0V to 3.7V) reduces power bus ringing (a source of EMI) and minimizes V_{CC} bounce and ground bounce and their effects during simultaneous output switching. The output configuration also enhances switching speed and is capable of sinking 64 milliamperes.

The CD74FCT540 is a three-state buffer having two active LOW output enables. The CD74FCT541 is a noninverting three state buffer having two active LOW output enables.

Ordering Information

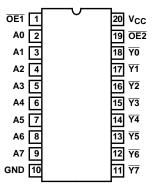
PART NUMBER	TEMP. RANGE (^O C)	PACKAGE	PKG. NO.
CD74FCT540E	0 to 70	20 Ld PDIP	E20.3
CD74FCT541E	0 to 70	20 Ld PDIP	E20.3
CD74FCT540M	0 to 70	20 Ld SOIC	M20.3
CD74FCT541M	0 to 70	20 Ld SOIC	M20.3
CD74FCT541SM	0 to 70	20 Ld SSOP	M20.209

NOTE: When ordering the suffix M and SM packages, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

Pinouts

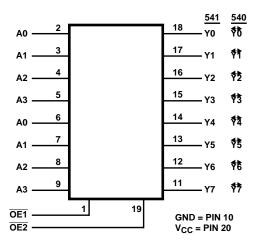
CD74FCT540 (PDIP, SOIC) TOP VIEW

CD74FCT541 (PDIP, SOIC, SSOP) TOP VIEW



OE1 1		20	٧cc
A0 2]	19	OE2
A1 3	1	18	Y0
A2 4]	17	Y1
A3 5]	16	Y2
A4 6]	15	Y3
A5 7]	14	Y4
A6 8	1	13	Y5
A7 9		12	Y6
GND 10	5	11	Y7

Functional Diagram



TRUTH TABLE (Note 1)

INPUTS			OUTPUTS		
OE1	OE2	A _n	CD74FCT540	CD74FCT541	
L	L	Н	L	Н	
Н	Х	X	Z	Z	
Х	Н	Х	Z	Z	
L	L	L	Н	L	

NOTE:

1. H = HIGH Voltage Level

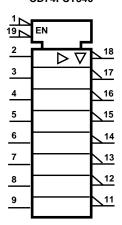
L = LOW Voltage Level

X = Immaterial

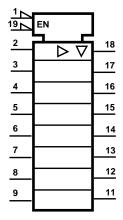
Z = HIGH Impedance

IEC Logic Symbol

CD74FCT540



CD74FCT541



Thermal Information

Thermal Resistance (Typical, Note 2)	θ _{JA} (°C/W)
PDIP Package	135
SOIC Package	125
SSOP Package	130
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range65	5°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC and SSOP-Lead Tips Only)	

Operating Conditions

Operating Temperature Range (T _A)	0°C to 70°C
Supply Voltage Range, V _{CC}	4.75V to 5.25V
DC Input Voltage, V ₁	0 to V _{CC}
DC Output Voltage, VO	0 to ≤ V _{CC}
Input Rise and Fall Slew Rate, dt/dv	0 to 10ns/V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Commercial Temperature Range 0° C to 70° C, V_{CC} Max = 5.25V, V_{CC} Min = 4.75V (Note 5)

					AMBIENT TEMPERATURE (T _A)				
		TEST CO	NDITIONS		25	°C	0°C TO	70°C	
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	MAX	MIN	MAX	UNITS
High Level Input Voltage	V _{IH}			4.75 to 5.25	2	-	2	-	V
Low Level Input Voltage	V _{IL}			4.75 to 5.25	-	0.8	-	0.8	V
High Level Output Voltage	V _{OH}	V_{IH} or V_{IL}	-15	Min	2.4	-	2.4	-	V
Low Level Output Voltage	V _{OL}	V _{IH} or V _{IL}	64	Min	-	0.55	-	0.55	V
High Level Input Current	I _{IH}	V _{CC}		Max	-	0.1	-	1	μА
Low Level Input Current	I _{IL}	GND		Max	-	-0.1	-	-1	μА
Three State Leakage Current	lozh	V _{CC}		Max	-	0.5	-	10	μА
	l _{OZL}	GND		Max	-	-0.5	-	-10	μА
Input Clamp Voltage	V _{IK}	V _{CC} or GND	-18	Min	-	-1.2	-	-1.2	V
Short Circuit Output Current (Note 3)	I _{OS}	V _O = 0 V _{CC} or GND		Max	-60	-	-60	-	mA
Quiescent Supply Current, MSI	Icc	V _{CC} or GND	0	Max	-	8	-	80	μΑ
Additional Quiescent Supply Current per Input Pin TTL Inputs High, 1 Unit Load	Δl _{CC}	3.4V (Note 4)		Max	-	1.6	-	1.6	mA

NOTES:

- 3. Not more than one output should be shorted at one time. Test duration should not exceed 100ms.
- 4. Inputs that are not measured are at $V_{\mbox{\footnotesize CC}}$ or GND.
- 5. FCT Input Loading: All inputs are 1 unit load. Unit load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 1.6mA Max. @ $70^{\circ}C$.

Switching Specifications Over Operating Range FCT Series t_r , t_f = 2.5ns, C_L = 50pF, R_L (Figure 3) (Note 6)

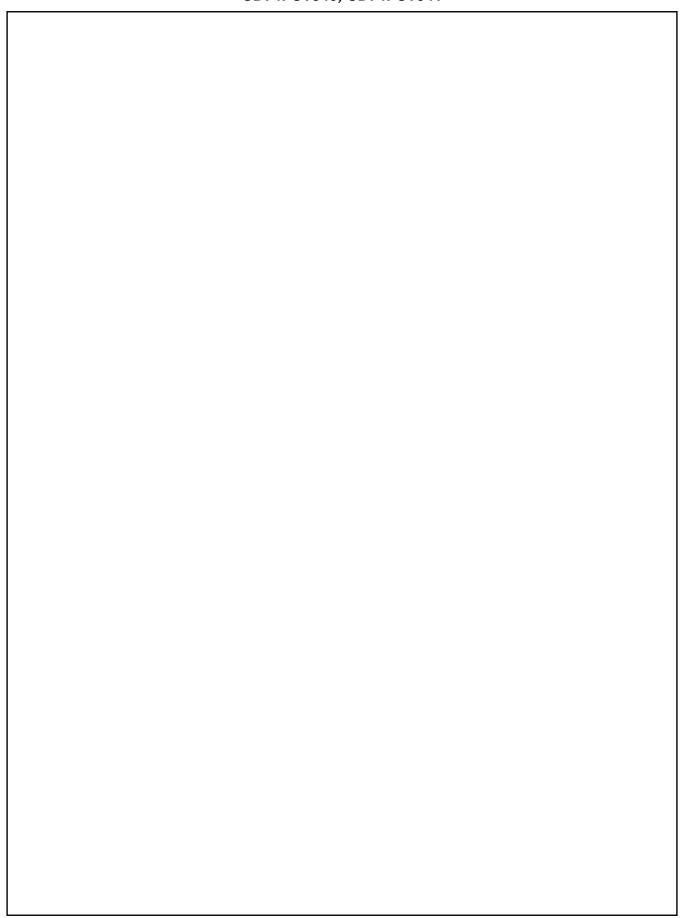
			25°C	0°C TO 70°C		
PARAMETER	SYMBOL	V _{CC} (V)	TYP	MIN	MAX	UNITS
Propagation Delays		(Note 6)				
Data to Outputs						
CD74FCT540	t _{PLH} , t _{PHL}	5	6.4	2	8.5	ns
CD74FCT541	t _{PLH} , t _{PHL}	5	6	2	8	ns
Output Disable to Output	t _{PLZ} , t _{PHZ}	5	7.1	2	9.5	ns
Output Enable to Output	t _{PZL} , t _{PZH}	5	7.5	2	10	ns
Power Dissipation Capacitance	C _{PD}					
CD74FCT540	(Note 7)	-	37	-	-	pF
CD74FCT541		-	40	-	-	pF
Minimum (Valley) V _{OHV} During Switching of Other Outputs (Output Under Test Not Switching)	V _{OHV}	5	0.5	-	-	V
Maximum (Peak) V _{OLP} During Switching of Other Outputs (Output Under Test Not Switching)	V _{OLP}	5	1	-	-	V
Input Capacitance	Cl	-	-	-	10	pF
Three-State Output Capacitance	CO	-	-	-	15	pF

NOTES:

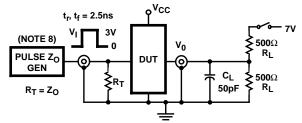
6. 5V: Min is at 5.25V for 0° C to 70° C, Max is at 4.75V for 0° C to 70° C, Typ is at 5V.

7. C_{PD}, measured per flip-flop, is used to determine the dynamic power consumption.
P_D (per package) = V_{CC} I_{CC} + Σ(V_{CC}² f_I C_{PD} + V_O² f_O C_L + V_{CC} ΔI_{CC} D) where:
V_{CC} = supply voltage
ΔI_{CC} = flow through current x unit load
C_L = output load capacitance
D = duty cycle of input high

f_O = output frequency f_I = input frequency



Test Circuits and Waveforms



NOTE:

8. Pulse Generator for All Pulses: Rate \leq 1.0MHz; $Z_{\mbox{OUT}} \leq$ 500; $t_{\mbox{f}},\,t_{\mbox{r}} \leq$ 2.5ns.

FIGURE 1. TEST CIRCUIT

SWITCH POSITION

TEST	SWITCH
t _{PLZ} , t _{PZL} , Open Drain	Closed
t _{PHZ} , t _{PZH} , t _{PLH} , t _{PHL}	Open

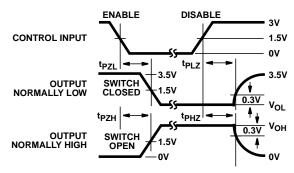
DEFINITIONS:

C_L = Load capacitance, includes jig and probe capacitance.

 R_T = Termination resistance, should be equal to $Z_{\mbox{OUT}}$ of the Pulse Generator.

 $V_{IN} = 0V$ to 3V.

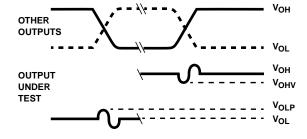
Input: $t_r = t_f = 2.5$ ns (10% to 90%), unless otherwise specified



3٧ SAME PHASE 1.5V INPUT TRANSITION οv tPLH ^tPHL v_{OH} OUTPUT 1.5V v_{oL} ^tPLH ^tPHI OPPOSITE PHASE 1.5V INPUT TRANSITION ٥v

FIGURE 2. ENABLE AND DISABLE TIMING

FIGURE 3. PROPAGATION DELAY



NOTES:

- 9. V_{OLP} is measured with respect to a ground reference near the output under test. V_{OHV} is measured with respect to V_{OH}.
- 10. Input pulses have the following characteristics:

 $P_{RR} \le 1MHz$, $t_r = 2.5ns$, $t_f = 2.5ns$, skew 1ns.

11. R.F. fixture with 700MHz design rules required. IC should be soldered into test board and bypassed with 0.1μF capacitor. Scope and probes require 700MHz bandwidth.

FIGURE 4. SIMULTANEOUS SWITCHING TRANSIENT WAVEFORMS

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